



Diode Module

Features

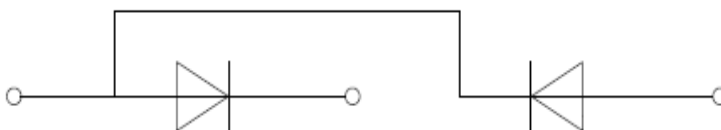
- A package of series of two diodes
- With high thermal conductivity DBC as the Insulation
- Welding by vacuum welding technology, which provide high reliability

Product Summary

Parameter	Value	Unit
V_{RRM}	2000	V
$I_{F(AV)}(@ T_C = 100^\circ\text{C})$	380	A
$I_{FSM}(@ t_p = 10\text{ms})$	12000	A
$V_F(\text{Max})$	1.60	V

Applications

- AC converter
- Inverter
- DC motor



Absolute Maximum Ratings (@ T_C)

Non-repetitive peak reverse voltage	$T_{vj} = 25^\circ\text{C}$	V_{RSM}	2100	V
Average forward current	$T_C = 100^\circ\text{C}$	$I_{F(AV)}$	380	A
Forward surge current	1/2 cycle, Sine wave, 50Hz $T_{vj} = 25$	I_{FSM}	12000	A
I^2t value for fusing		I^2t	720000	A^2s
RMS isolation voltage	A.C 50Hz(1s/1min)	V_{ISO}	3600/3000	V
Junction temperature range		T_J	-40 ~ +150	
Storage temperature range		T_{stg}	-40 ~ +125	



Electrical Characteristics (@ T_C = 25°C unless otherwise specified)

		Symbol	Values	Unit
				6 693644 f C7 -

Typical Electrical & Thermal Characteristics

FIG.1: Forward characteristics (per diode)

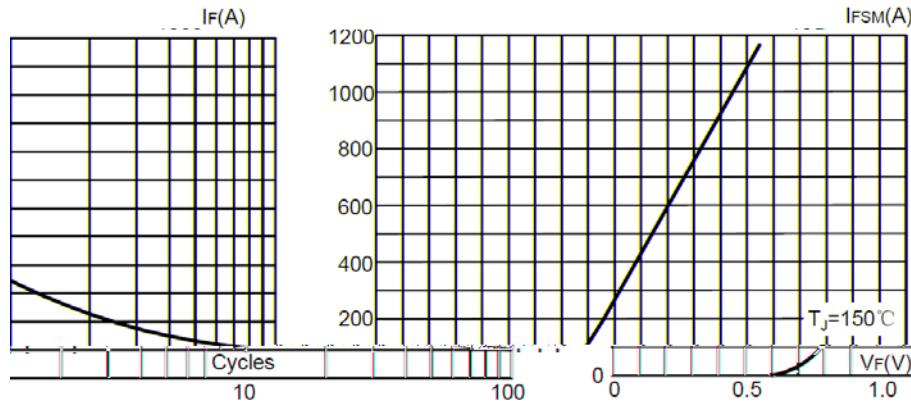


FIG.2: Peak on-state surge current

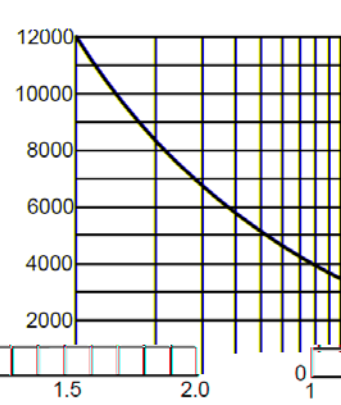


FIG.3: Forward current vs. case temperature

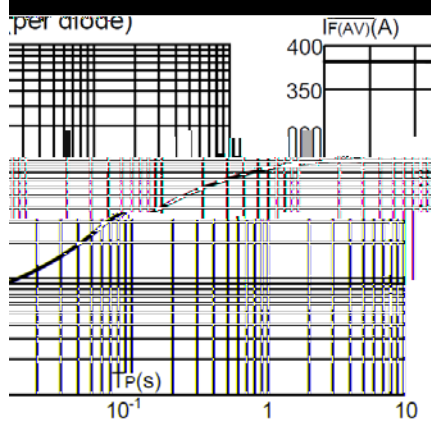
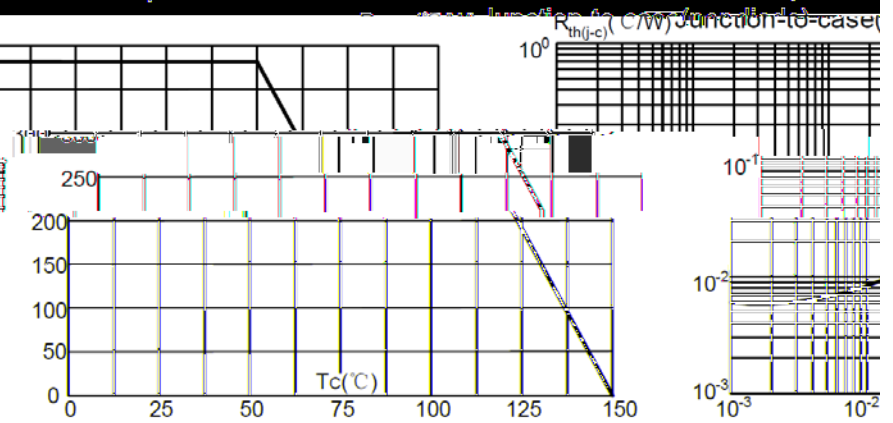
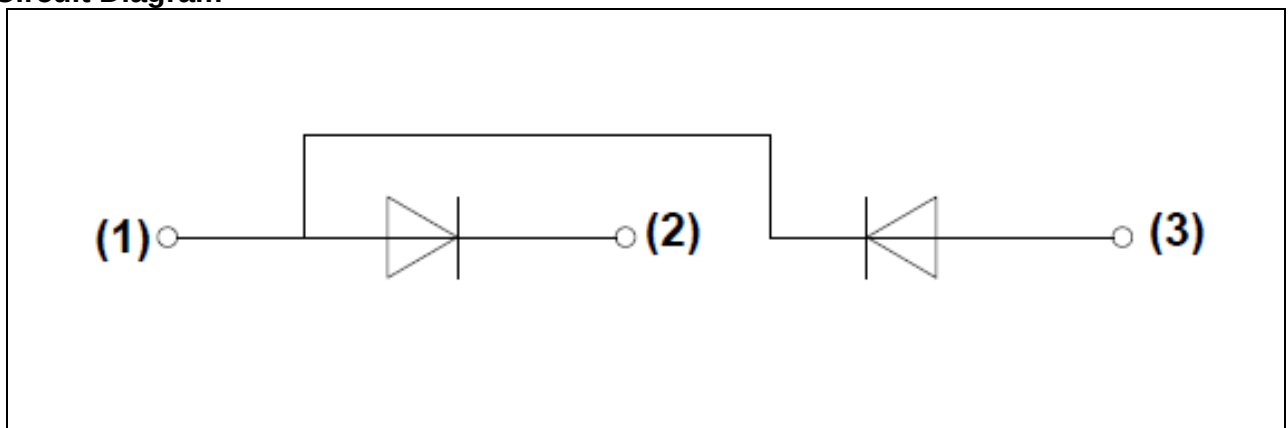
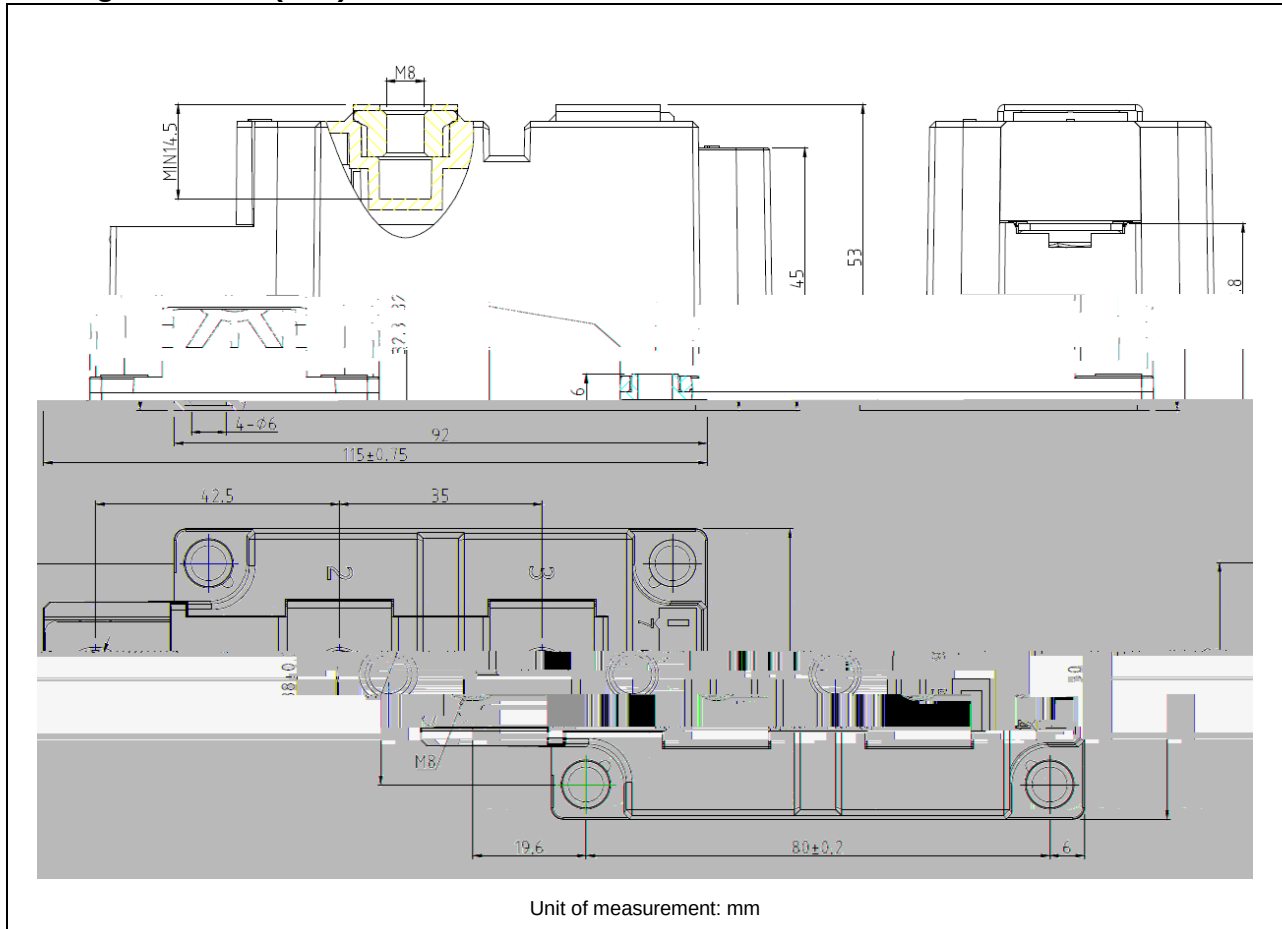


FIG.4: Maximum transient thermal impedance



Circuit Diagram



Package Outlines (mm)




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